Electronic Supplementary Information (ESI)

Tuning Band Gaps of BN Nanosheets and Nanoribbons via Interfacial Dihalogen Bonding and External Electric Field

Qing Tang,^{a,b} Jie Bao,^a Yafei Li,^c Zhen Zhou^{*a} and Zhongfang Chen^{*b}

^a Tianjin Key Laboratory of Metal and Molecule Based Material Chemistry, Key Laboratory of Advanced Energy Materials Chemistry (Ministry of Education), Computational Centre for Molecular Science, Institute of New Energy Material Chemistry, Collaborative Innovation Center of Chemical Science and Engineering (Tianjin), Nankai University, Tianjin 300071, P. R. China. Email: zhouzhen@nankai.edu.cn

^b Department of Chemistry, Institute for Functional Nanomaterials, University of Puerto Rico, Rio Piedras Campus, San Juan, PR 00931. Email: zhongfangchen@gmail.com

^c Nanjing Normal University, Department of Chemistry, Nanjing 210042, China



Fig. S1 Phonon dispersion structure of monolayer fluoro-BN (a) and chloro-BN (b).



Fig. S2 Partial charge densities of VBM (left) and CBM (right) states at the Γ point for monolayer fluoro-BN (a), AB-stacked bilayer fluoro-BN with interlayer B-F…F-N (b), B-F…F-B (c), and N-F…F-N (d) connections. (e) to (h) correspond to the VBM and CBM distributions of monolayer chloro-BN, AB-stacked bilayer chloro-BN with interlayer B-Cl…Cl-N, B-Cl…Cl-B, and N-Cl…Cl-N connections, respectively.



Fig. S3 The band gap of partially fluorinated (a) and chlorinated (b) BN monolayers and bilayers as a function of fluorination or chlorination ratio, and the bilayer structures corresponding to different ratios are shown in the inset.



Fig. S4 Band structure of hybrid fluoro-BN/chloro-BN bilayer based on HSE06 computations with a mixing parameter of 0.2 (a) and 0.15 (b), respectively.